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Concl.

an electrode of one conductivity type which is formed on said substrate;
an intermediate layer formed on said electrode of the one conductivity type, containing at least one of In, Ag, Ni and Cr;
a reflective layer which is formed on said intermediate layer, contains a metal, and reflects a light;
a light-emitting layer formed on said reflective layer to emit light, having a double-heterostructure in which an active layer is sandwiched between first and second cladding layers;
and
a transparent electrode formed on said light-emitting layer to transmit light.

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5. (amended) An element according to claim 1, further comprising a contact layer of the one conductivity type and a strain relaxing layer, formed between said reflective layer and said light-emitting layer, wherein said strain relaxing layer has a middle band gap between band gaps of said contact layer of the one conductivity type and said first cladding layer.

6. (amended) An element according to claim 1, further comprising a contact layer of an opposite conductivity type formed between said light-emitting layer and said transparent electrode, containing InGaP or InGaAlP.

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17. (amended) A semiconductor light-emitting element comprising:
a transparent semiconductor substrate;
a double-heterostructure which is formed on said semiconductor substrate and contains a light-emitting layer and first and second cladding layers that sandwich two surfaces of the light-emitting layer;
a contact layer which is formed on said double-heterostructure and has a recessed surface; and
a light-reflecting electrode formed on the recessed surface of said contact layer.

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20. (amended) A semiconductor light-emitting diode comprising at least a light-emitting layer formed on a semiconductor substrate,

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wherein a shape of said semiconductor light-emitting element is a polygonal prism having at least five corners or a circular cylinder.

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25. (amended) A semiconductor light-emitting element comprising:
a semiconductor substrate;
a light-emitting layer formed on one surface of said semiconductor substrate; and
a photonics crystal layer fused on another surface of said semiconductor substrate,
wherein the other surface of said semiconductor substrate has a rounded edge.